



SOT-89-3L Plastic-Encapsulate Transistors

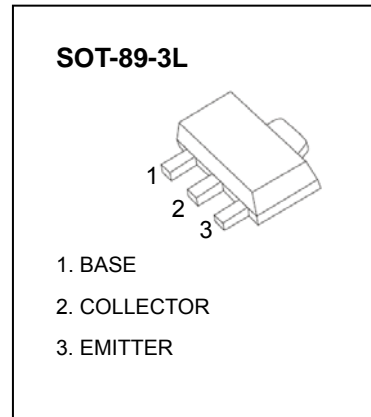
A94 TRANSISTOR (PNP)

FEATURES

High voltage

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-400	V
V _{CEO}	Collector-Emitter Voltage	-400	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.2	A
I _{CM}	Collector Current- Pulsed	-0.3	A
P _C	Collector Power Dissipation	0.5	W
T _J	Junction Temperature	150	°C
T _{stg}	storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR) CBO}	I _C = -100μA, I _E =0	-400			V
Collector-emitter breakdown voltage	V _{(BR) CEO}	I _C = -1mA, I _B =0	-400			V
Emitter-base breakdown voltage	V _{(BR) EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-400V, I _E =0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-400V, I _B =0			-5	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-10V, I _C =-10mA	80		300	
	h _{FE(2)}	V _{CE} =-10V, I _C =-1mA	70			
	h _{FE(3)}	V _{CE} =-10V, I _C =-100mA	60			
	h _{FE(4)}	V _{CE} =-10V, I _C =-50mA	80			
Collector-emitter saturation voltage	V _{CE (sat)}	I _C =-10mA, I _B =-1mA			-0.2	V
	V _{CE (sat)}	I _C =-50mA, I _B =-5mA			-0.3	V
Base-emitter saturation voltage	V _{BE (sat)}	I _C =-10mA, I _B = -1mA			-0.75	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA f =30MHz	50			MHz

Typical Characteristics

A94

